

# 2SC535

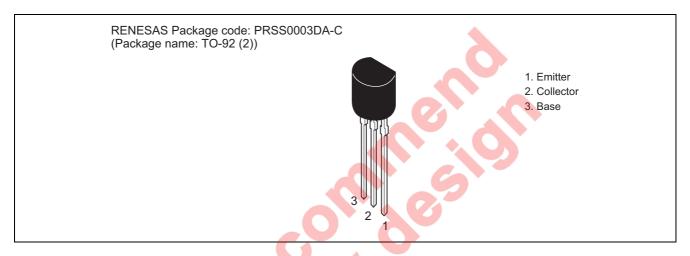
# Silicon NPN Epitaxial Planar

REJ03G0683-0200 (Previous ADE-208-1047) Rev.2.00 Aug.10.2005

### **Application**

VHF amplifier, mixer, local oscillator

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	30	V
Collector to emitter voltage	$V_{\sf CEO}$	20	V
Emitter to base voltage	$V_{EBO}$	4	V
Collector current	Ic	20	mA
Collector power dissipation	Pc	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

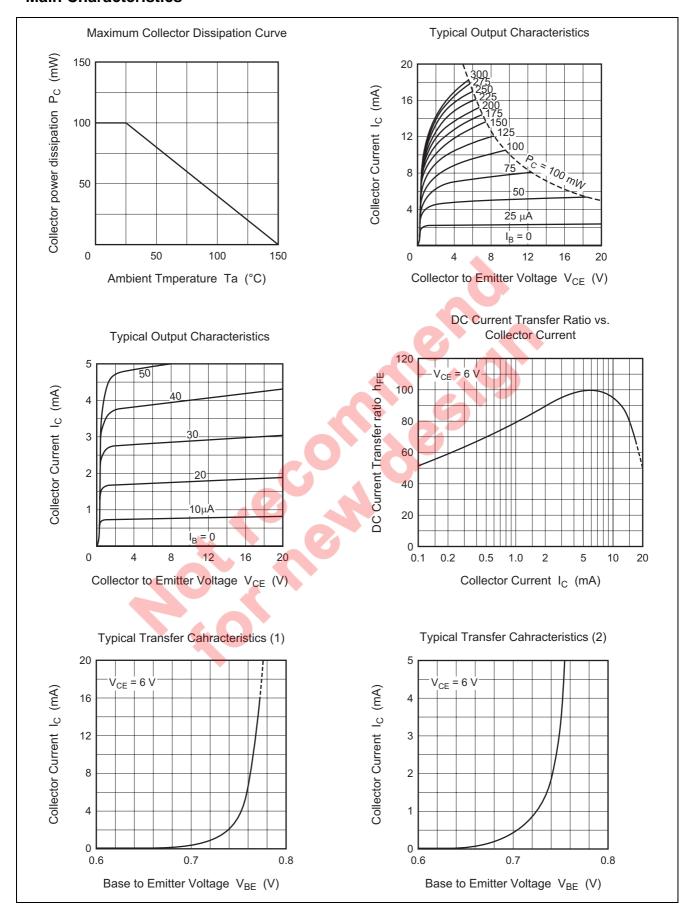
#### **Electrical Characteristics**

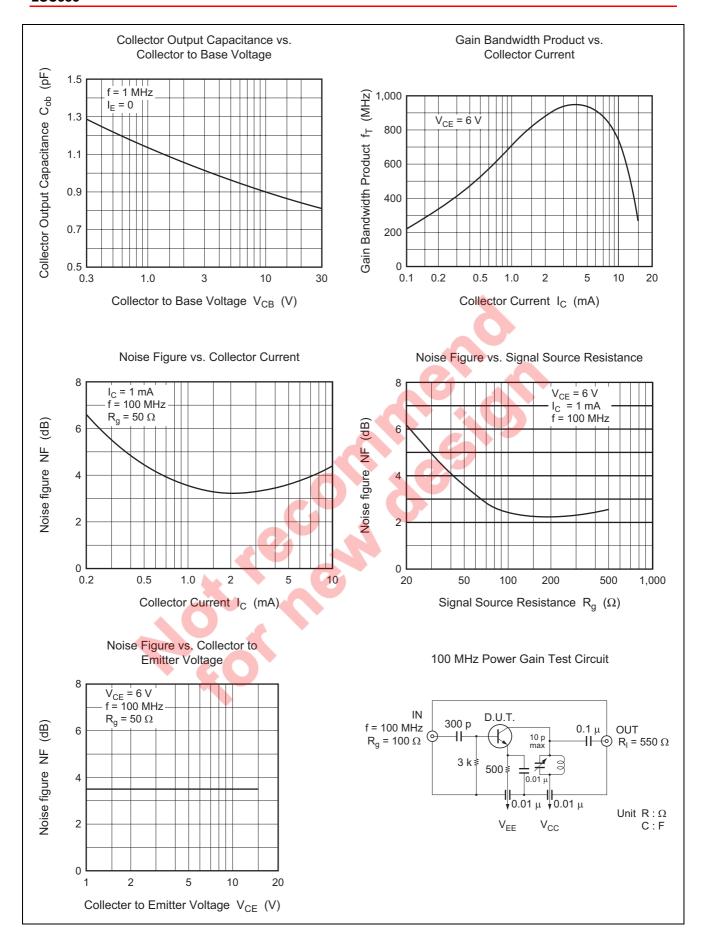
 $(Ta = 25^{\circ}C)$ 

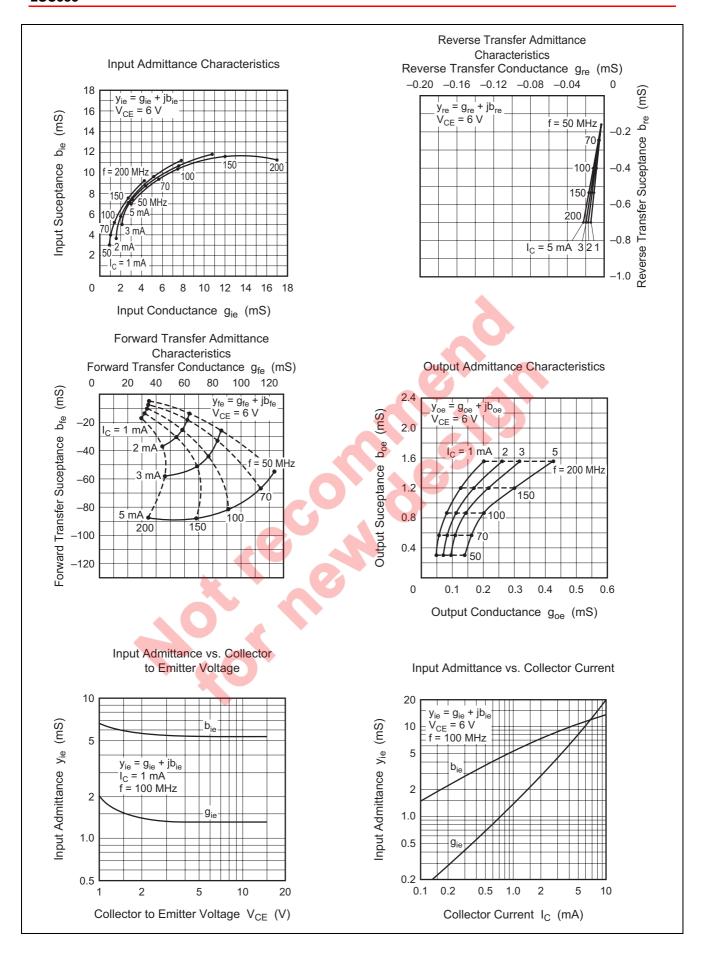
	Min	Тур	Max	Unit	Test conditions	
V <sub>(BR)CBO</sub>	30	_	_	V	$I_C = 10 \mu\text{A},  I_E = 0$	
V <sub>(BR)CEO</sub>	20	_	_	V	I <sub>C</sub> = 1 mA, R <sub>BE</sub> = ∞	
V <sub>(BR)EBO</sub>	4	_	_	V	$I_E = 10 \mu A, I_C = 0$	
I <sub>CBO</sub>	_	_	0.5	μΑ	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0	
h <sub>FE</sub> *1	60	_	200		V <sub>CE</sub> = 6 V, I <sub>C</sub> = 1 mA	
V <sub>BE</sub>	_	0.72	_	V	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$	
V <sub>CE(sat)</sub>	_	0.17	_	V	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$	
f⊤	450	940	_	MHz	$V_{CE} = 6 \text{ V}, I_C = 5 \text{ mA}$	
Cob	_	0.9	1.2	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	
PG	17	20		dB	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ f = 100 MHz	
NF	_	3.5	5.5	dB	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ $f = 100 \text{ MHz}, R_{g} = 50 \Omega$	
yie		1.3 + j5.3		mS	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ f = 100 MHz	
yre	-0	.078 – j0.	41	mS		
yfe		32 – j10		mS		
yoe	0	.08 + j0.8	2	mS		
<sub>FE</sub> as follows	-			A		
B C 60 to 120 100 to 200						
	V(BR)CEO V(BR)EBO ICBO hFE*1 VBE VCE(sat) fT COb PG NF yie yre yfe yoe nFE as follows	V(BR)CEO         20           V(BR)EBO         4           ICBO         —           hFE*1         60           VBE         —           VCE(sat)         —           fT         450           Cob         —           PG         17           NF         —           yie         yre           yre         —           yfe         yoe           0         0           nFE         as follows.	V(BR)CEO         20         —           V(BR)EBO         4         —           ICBO         —         —           hFE*1         60         —           VBE         —         0.72           VCE(sat)         —         0.17           fT         450         940           Cob         —         0.9           PG         17         20           NF         —         3.5           yie         1.3 + j5.3           yre         —0.078 – j0.           yfe         32 – j10           yoe         0.08 + j0.8	V(BR)CEO         20         —         —           V(BR)EBO         4         —         —           ICBO         —         —         0.5           hFE* <sup>1</sup> 60         —         200           VBE         —         0.72         —           VCE(sat)         —         0.17         —           fT         450         940         —           Cob         —         0.9         1.2           PG         17         20         —           NF         —         3.5         5.5           yie         1.3 + j5.3         —           yre         —0.078 – j0.41         —           yfe         32 – j10         —           yoe         0.08 + j0.82         —	V(BR)CEO       20       —       —       V         V(BR)EBO       4       —       —       V         ICBO       —       —       0.5       μA         hFE**       60       —       200         VBE       —       0.72       —       V         VCE(sat)       —       0.17       —       V         fT       450       940       —       MHz         Cob       —       0.9       1.2       pF         PG       17       20       —       dB         NF       —       3.5       5.5       dB         yie       1.3 + j5.3       mS         yre       —0.078 – j0.41       mS         yre       32 – j10       mS         yre       0.08 + j0.82       mS         nee       as follows.	

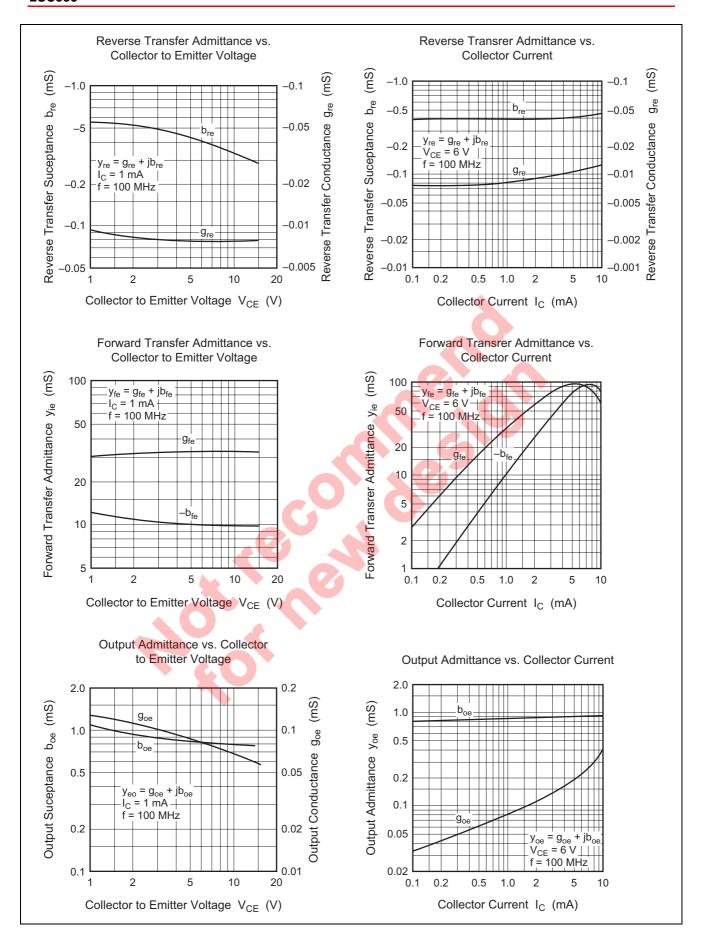
В	С	
60 to 120	100 to 200	

#### **Main Characteristics**

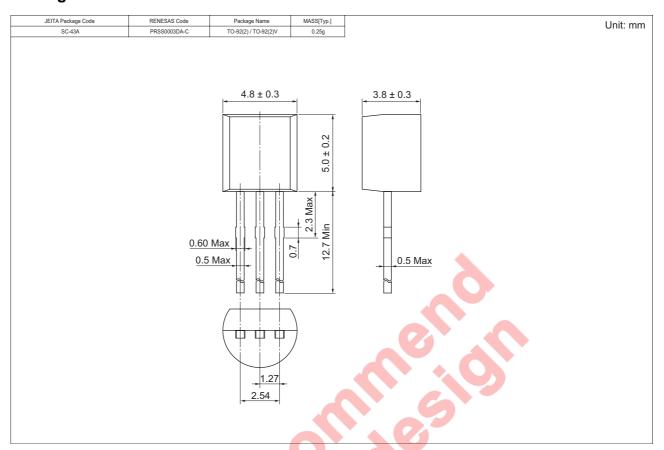








### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
2SC535BTZ	2500	Hold Box, Radial Taping
2SC535CTZ		

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